RF Broadcast and ISM (Industrial, Scientific and Medical)

NXP's new 65 V LDMOS technology: designed for ease of use.

**The Five Benefits of 65 V LDMOS**

1. **More power** - Higher voltage enables higher power density, which helps reduce the number of transistors to combine.

2. **Faster development time** - With higher voltage, the output power can be increased while retaining a reasonable output impedance.

3. **Design Reuse** - This impedance benefit also ensures pin-compatibility with current 50 V LDMOS transistors for better scalability.

4. **Manageable current level** - Higher voltage reduces the current losses in the system.

5. **Wide safety margin** - The higher breakdown voltage of 182 V improves ruggedness and allows for higher efficiency classes of operation.

**MRFX series**

- **MRFX1K80H**
  - 1800 W CW, 1.8-470 MHz, Up to 65 V
  - Air-Cavity Ceramic Packaging
  - Samples available now

- **MRFX1K80N**
  - 1800 W CW, 1.8-4700 MHz, Up to 65 V
  - Over-Molded Plastic Packaging with low thermal resistance
  - Samples available in Q3 2017

**65V Introduction**

Learn more about our 65 V technology and the MRFX1K80

**Press Release**

NXP announces a new LDMOS technology

For samples and further requests click here.

Want to see more? Visit our RF Power Transistors web site.